ALPHA & OMEGA SEMICONDUCTOR

AOL1414
N-Channel Enhancement Mode Field Effect Transistor

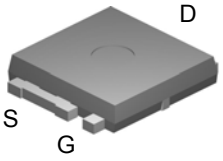
General Description

The AOL1414 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate chargeand low gate resistance. This device is ideally suited for use as a high side switch in CPU core power conversion. *Standard Product AOL1414 is Pb-free (meets ROHS & Sony 259 specifications). AOL1414L is a Green Product ordering option. AOL1414 and AOL1414L are electrically identical.*

Features

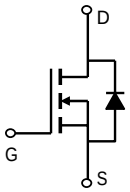
V_{DS} (V) = 30V
I_D = 85A (V_{GS} = 10V)
$R_{DS(ON)}$ < 6.5mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 7.5mΩ (V_{GS} = 4.5V)

Ultra SO-8™ Top View



Bottom tab connected to drain

Fits SOIC8 footprint !



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current [B]	T_C=25°C	I_D	85	A
	T_C=100°C		70	
Pulsed Drain Current		I_{DM}	200	
Continuous Drain Current [G]	T_A=25°C	I_{DSM}	15	
	T_A=70°C		12	
Avalanche Current [C]		I_{AR}	30	A
Repetitive avalanche energy L=0.3mH [C]		E_{AR}	135	mJ
Power Dissipation [B]	T_C=25°C	P_D	100	W
	T_C=100°C		50	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.5	W
	T_A=70°C		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	19.5	25	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		48	60	°C/W
Maximum Junction-to-Case [C]	Steady-State	$R_{\theta JC}$	1	1.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V		0.002	1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1	1.5	2	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	100			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		4.9	6.5	mΩ
		T_J=125°C		6.9	8.3	
		V_{GS}=4.5V, I_D=20A		6	7.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		90		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		2100	2520	pF
C_{oss}	Output Capacitance			536		pF
C_{rss}	Reverse Transfer Capacitance			165		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.95	1.5	Ω
SWITCHING PARAMETERS						
Q_g(4.5V)	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=20A		19.7	24	nC
Q_{gs}	Gate Source Charge			3.6		nC
Q_{gd}	Gate Drain Charge			7.9		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		5.9	10	ns
t_r	Turn-On Rise Time			11	17	ns
$t_{D(off)}$	Turn-Off DelayTime			36.2	55	ns
t_f	Turn-Off Fall Time			12	18	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/µs		35	42	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/µs		33	50	nC

A: The value of R qJA is measured with the device in a still air environment with T A =25°C.
B. The power dissipation PD is based on TJ(MAX)=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C: Repetitive rating, pulse width limited by junction temperature TJ(MAX)=175°C.
D. The R qJA is the sum of the thermal impedence from junction to case R qJC and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C.
G. The maximum current rating is limited by bond-wires.
H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T A=25°C. The SOA curve provides a single pulse rating.
Rev1: Dec. 2005

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

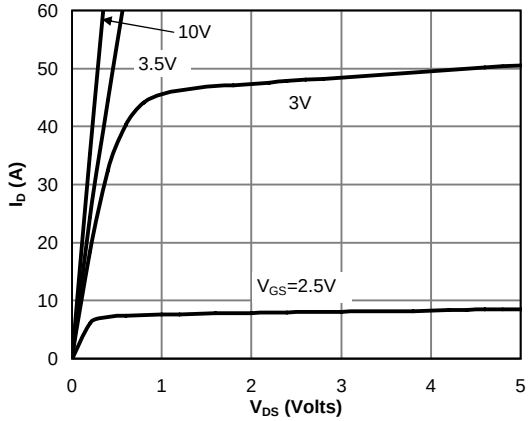


Fig 1: On-Region Characteristics

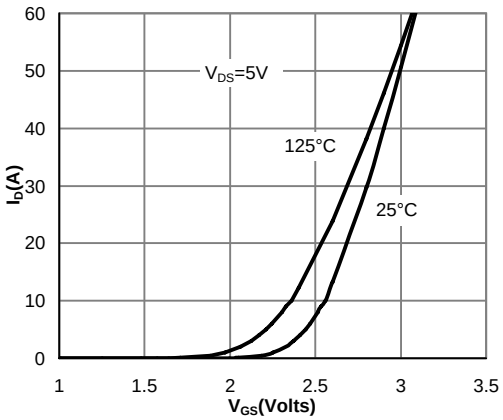


Figure 2: Transfer Characteristics

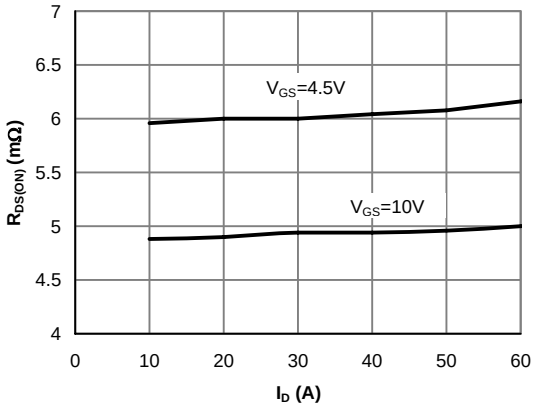


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

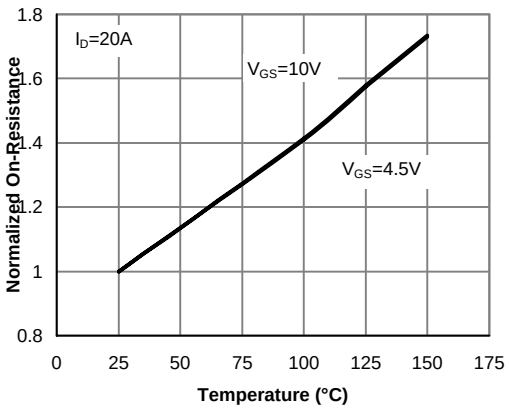


Figure 4: On-Resistance vs. Junction Temperature

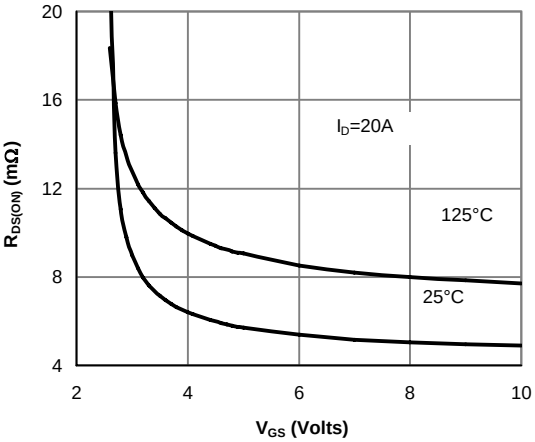


Figure 5: On-Resistance vs. Gate-Source Voltage

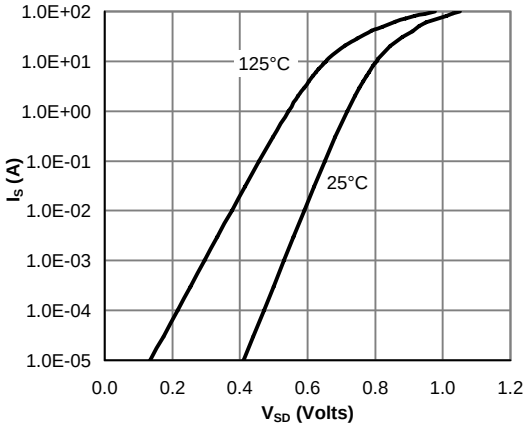


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

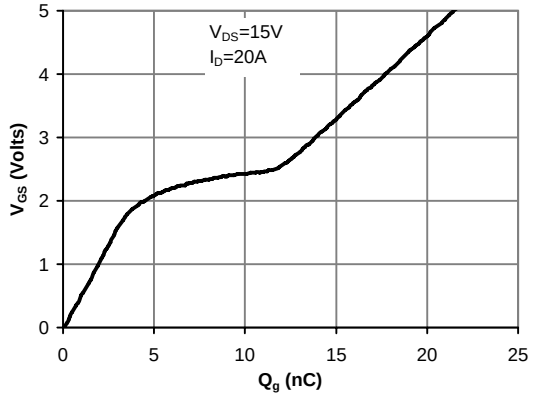


Figure 7: Gate-Charge Characteristics

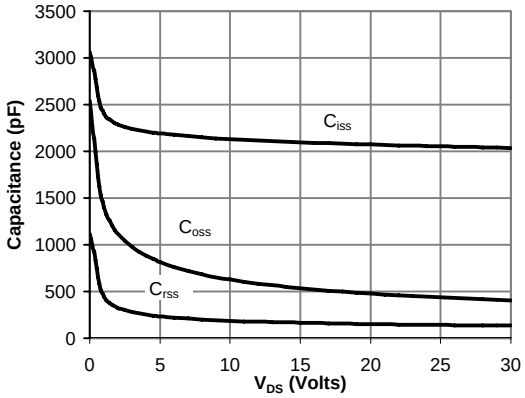


Figure 8: Capacitance Characteristics

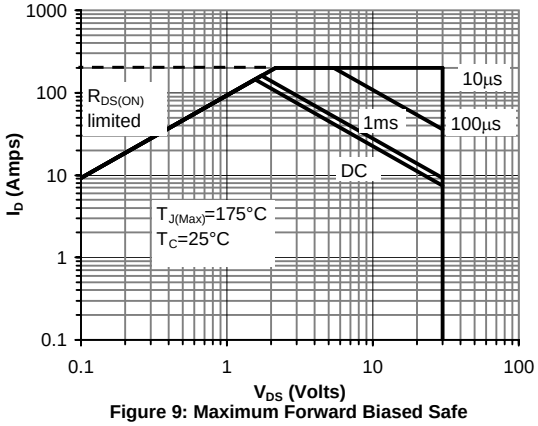


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

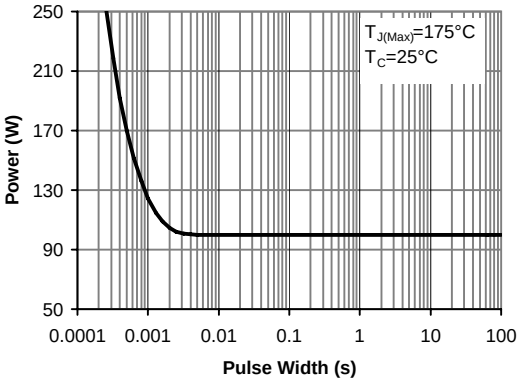


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

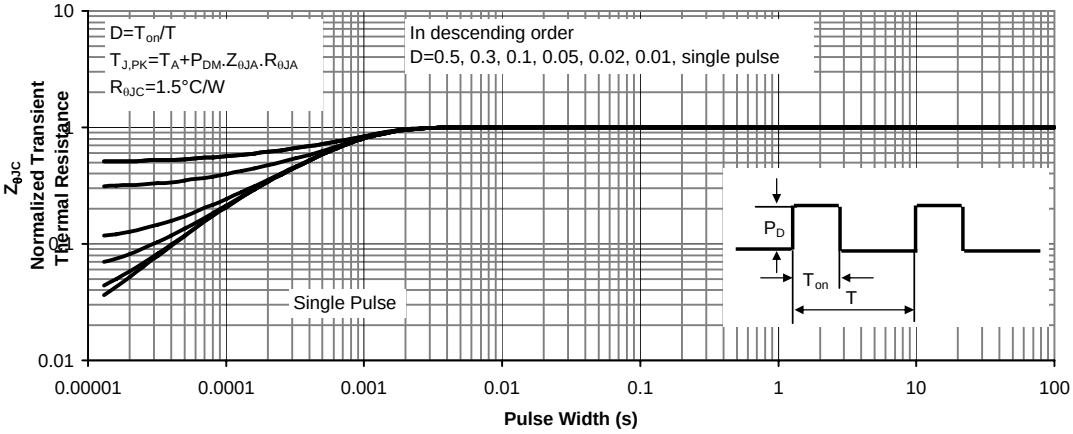


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

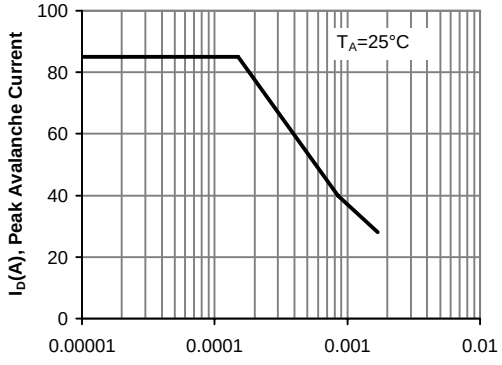


Figure 12: Single Pulse Avalanche capability

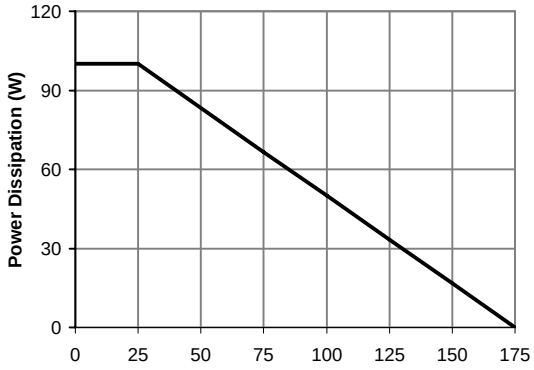


Figure 13: Power De-rating (Note B)

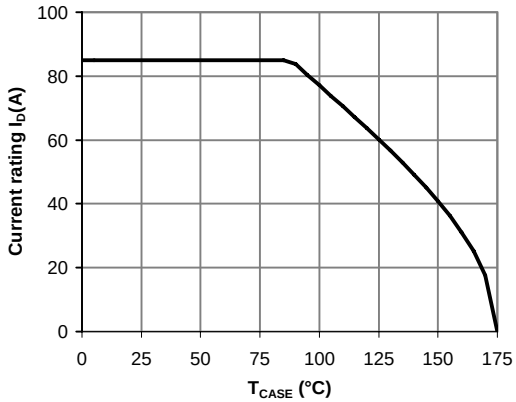


Figure 14: Current De-rating (Note B)

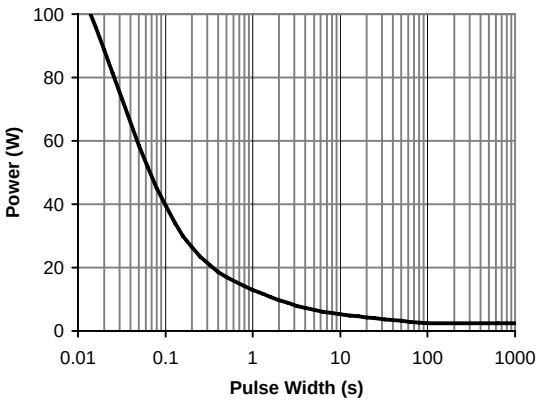


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

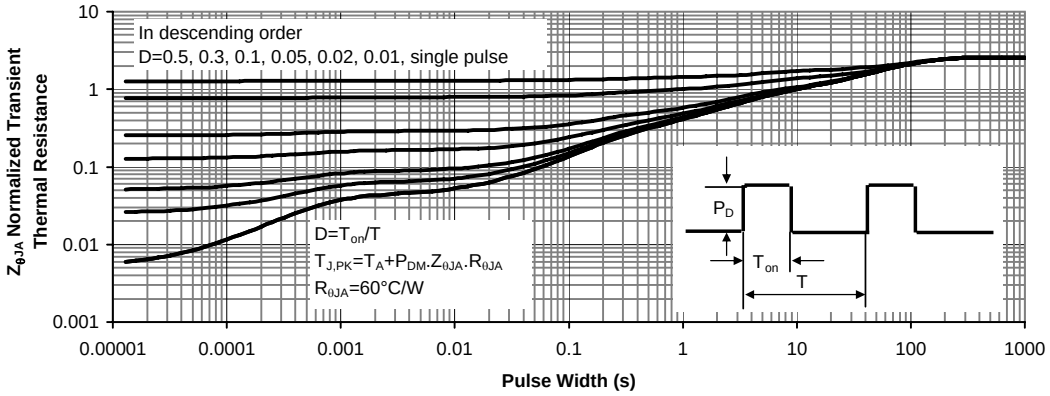


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)